CD40106B Types

CMOS Hex Schmitt Triggers

High-Voltage Types (20-Volt Rating)

The RCA-CD40106B consists of six Schmitt-trigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive- and negative-going signals. The difference between the positive-going voltage (VP) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig.6).

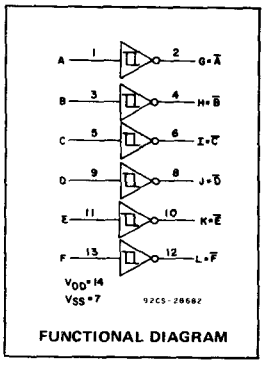
The CD40106B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), 14-lead ceramic flat package (K suffix), and in chip form (H suffix).

Features:

- **Schmitt-trigger action with no external components**
- **Hysteresis voltage (typ.) 0.9 V at V_{DD} = 5 V, 2.3 V at V_{DD} = 10 V, and 3.5 V at V_{DD} = 15 V**
- **Noise immunity greater than 50%**
- **No limit on input rise and fall times**
- **Standardized, symmetrical output characteristics**
- **100% tested for quiescent current at 20 V**
- **Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C**
- **Low V_{DD} to V_{SS} current during slow input ramp**
- **5-V, 10-V, and 15-V parametric ratings**
- **Meets all requirements of JEDEC Tentative Standard No.13A, "Standard Specifications for Description of 'B' Series CMOS Devices"**

Applications:

- **Wave and pulse shapers**
- **High-noise-environment systems**
- **Monostable multivibrators**
- **Astable multivibrators**



FUNCTIONAL DIAGRAM

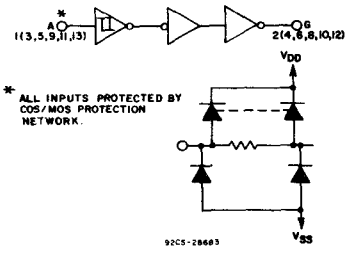


Fig.1 – Logic diagram (1 of 6 Schmitt triggers).

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -40 to +60°C (PACKAGE TYPE E) ..... 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) ..... Derate Linearly at 12 mW/°C to 200 mW
For T_A = -55 to +100°C (PACKAGE TYPES D, F, K) ..... 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K) ..... Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:
For T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H ..... -55 to +125°C
PACKAGE TYPE E ..... -40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. ..... +265°C

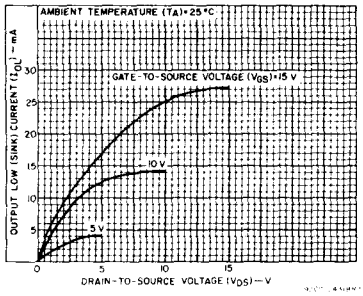


Fig.2 – Typical output low (sink) current characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A Full Package-Temperature Range)	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C, Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS		LIMITS		UNITS
		V_{DD} (V)	TYP.	MAX.	
Propagation Delay Time:		5	140	280	
t_{PHL},		10	70	140	ns
t_{PLH}		15	60	120	
Transition Time:		5	100	200	
t_{THL},		10	50	100	ns
t_{TLH}		15	40	80	
Input Capacitance, C_{IN}	Any Input		5	7.5	pF

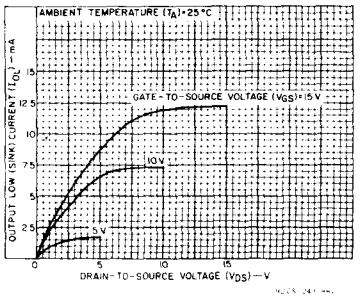


Fig.3 – Minimum output low (sink) current characteristics.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at -55, +25, +125 Apply to D, F, K, H, Packages Values at -40,+25,+85 Apply to E Packages							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	-55	-40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Positive Trigger Threshold Voltage V_P Min.	–	–	5	2.2	2.2	2.2	2.2	2.2	2.9	–	V
	–	–	10	4.6	4.6	4.6	4.6	4.6	5.9	–	
	–	–	15	6.8	6.8	6.8	6.8	6.8	8.8		
V_P Max.	–	–	5	3.6	3.6	3.6	3.6	–	2.9	3.6	
	–	–	10	7.1	7.1	7.1	7.1	–	5.9	7.1	
	–	–	15	10.8	10.8	10.8	10.8	–	8.8	10.8	
Negative Trigger Threshold Voltage V_N Min.	–	–	5	0.9	0.9	0.9	0.9	0.9	1.9	–	V
	–	–	10	2.5	2.5	2.5	2.5	2.5	3.9	–	
	–	–	15	4	4	4	4	4	5.8	–	
V_N Max.	–	–	5	2.8	2.8	2.8	2.8	–	1.9	2.8	
	–	–	10	5.2	5.2	5.2	5.2	–	3.9	5.2	
	–	–	15	7.4	7.4	7.4	7.4	–	5.8	7.4	
Hysteresis Voltage V_H Min.	–	–	5	0.3	0.3	0.3	0.3	0.3	0.9	–	V
	–	–	10	1.2	1.2	1.2	1.2	1.2	2.3	–	
	–	–	15	1.6	1.6	1.6	1.6	1.6	3.5	–	
V_H Max.	–	–	5	1.6	1.6	1.6	1.6	–	0.9	1.6	
	–	–	10	3.4	3.4	3.4	3.4	–	2.3	3.4	
	–	–	15	5	5	5	5	–	3.5	5	
Output Low (Sink) Current, I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0.5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	-	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	-	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage Low-Level, V_{OL} Max.	–	5	5	0.05				–	0	0.05	V
	–	10	10	0.05				–	0	0.05	
	–	15	15	0.05				–	0	0.05	
Output Voltage High Level, V_{OH} Min.	–	0	5	4.95				4.95	5	–	
	–	0	10	9.95				9.95	10	–	
	–	0	15	14.95				14.95	15	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

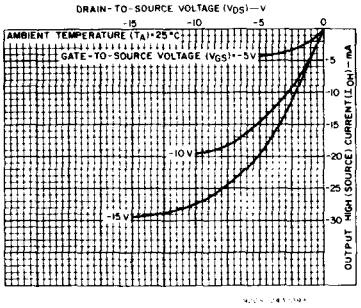


Fig.4 – Typical output high (source) current characteristics.

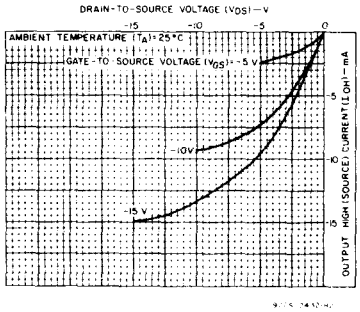


Fig.5 – Minimum output high (source) current characteristics.

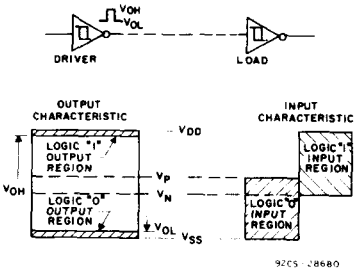
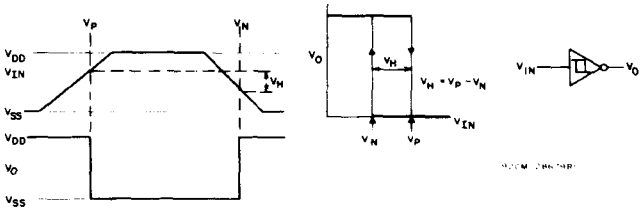


Fig.7 – Input and output characteristics.



a) Definition of V_P, V_N, V_H *b) Transfer characteristics of 1 of 6 gates*

Fig.6 – Hysteresis definition, characteristics, and test set-up.

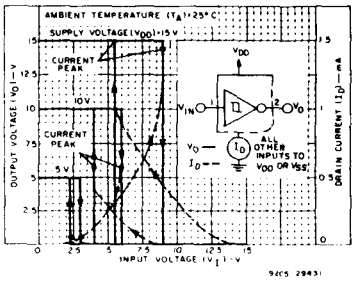


Fig.8 – Typical current and voltage transfer characteristics.

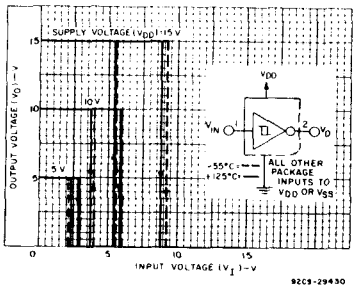


Fig.9 – Typical voltage transfer characteristics as a function of temperature.

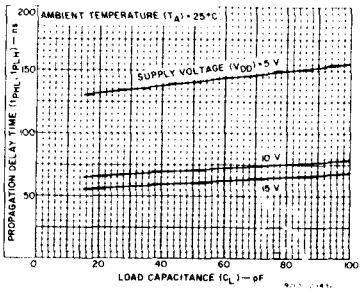


Fig.10 – Typical propagation delay time as a function of load capacitance.

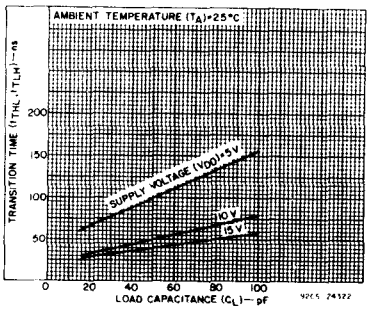


Fig.11 – Typical transition time as a function of load capacitance.

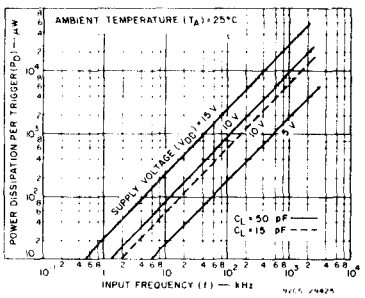


Fig.12 – Typical power dissipation per trigger as a function of input frequency.

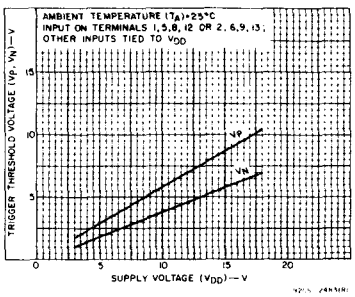


Fig.13 – Typical trigger threshold voltage as a function of supply voltage.

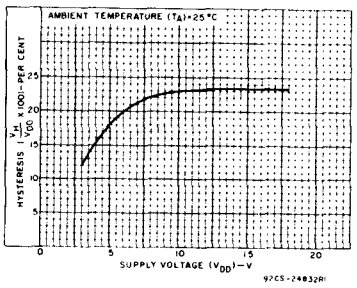


Fig.14 – Typical per cent hysteresis as a function of supply voltage.

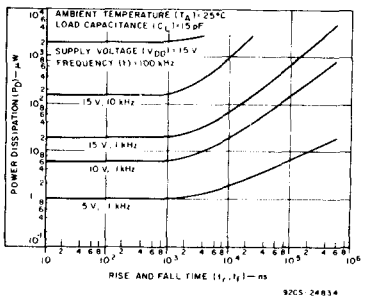


Fig.15 – Typical power dissipation as a function of rise and fall times.

APPLICATIONS

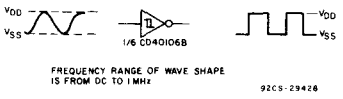


Fig.16 – Wave shaper.

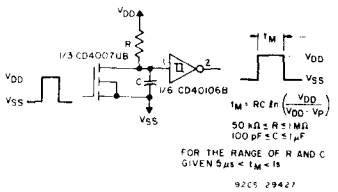


Fig.17 – Monostable multivibrator.

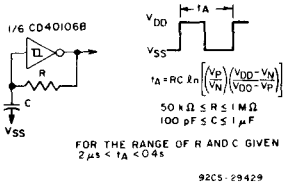


Fig.18 – Astable multivibrator.

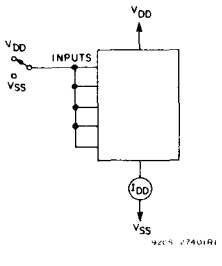


Fig.19 – Quiescent device current test circuit.

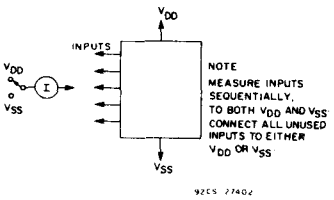


Fig.20 – Input current test circuit.

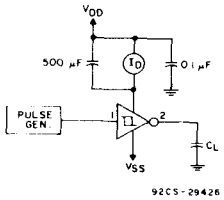
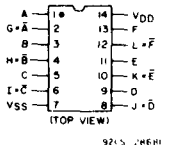
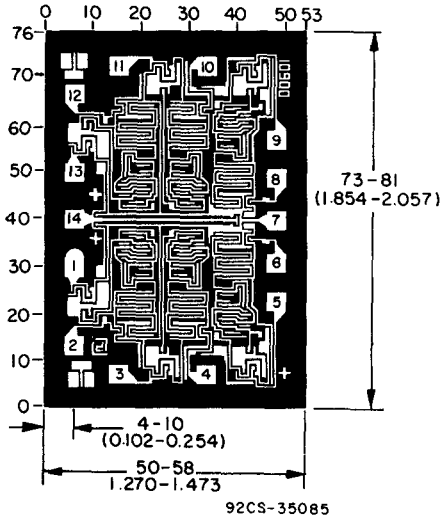


Fig.21 – Dynamic power dissipation test circuit.



TERMINAL ASSIGNMENT



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.

Dimensions and Pad Layout for CD40106BH